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FAIRCHILD SEMICONDUCTOR®

QFET™

FQP6N90C/FQPF6N90C

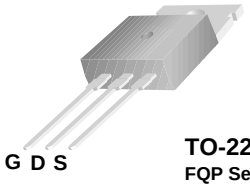
900V N-Channel MOSFET

General Description

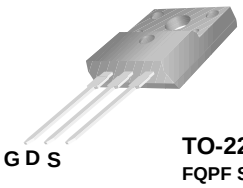
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supplies.

Features

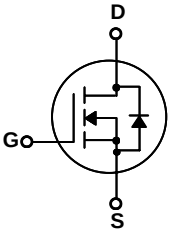
- 6A, 900V, $R_{DS(on)}$ = 2.3Ω @V_{GS} = 10 V
- Low gate charge (typical 30 nC)
- Low Crss (typical 11 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



TO-220
FQP Series



TO-220F
FQPF Series



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter		FQP6N90C	FQPF6N90C	Units
V_{DSS}	Drain-Source Voltage		900		V
I_D	Drain Current - Continuous (T_C = 25°C)		6	6 *	A
	Drain Current - Continuous (T_C = 100°C)		3.8	3.8 *	A
I_{DM}	Drain Current - Pulsed	(Note 1)	24	24 *	A
V_{GSS}	Gate-Source Voltage		± 30		V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	650		mJ
I_{AR}	Avalanche Current	(Note 1)	6		A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	16.7		mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5		V/ns
P_D	Power Dissipation (T_C = 25°C)		167	56	W
	- Derate above 25°C		1.43	0.48	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300		°C

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FQP6N90C	FQPF6N90C	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.75	2.25	°C/W
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	°C/W

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Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	900	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	--	1.07	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 900 V, V_{GS} = 0 V	--	--	10	μA
		V_{DS} = 720 V, T_C = 125°C	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 3 A	--	1.93	2.3	Ω
g_{FS}	Forward Transconductance	V_{DS} = 50 V, I_D = 3 A (Note 4)	--	5.5	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	1360	1770	pF
C_{oss}	Output Capacitance		--	110	145	pF
C_{rss}	Reverse Transfer Capacitance		--	11	15	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 450 V, I_D = 6 A, R_G = 25 Ω (Note 4, 5)	--	35	80	ns
t_r	Turn-On Rise Time		--	90	190	ns
$t_{d(off)}$	Turn-Off Delay Time		--	55	120	ns
t_f	Turn-Off Fall Time		--	60	130	ns
Q_g	Total Gate Charge	V_{DS} = 720 V, I_D = 6 A, V_{GS} = 10 V (Note 4, 5)	--	30	40	nC
Q_{gs}	Gate-Source Charge		--	9.0	--	nC
Q_{gd}	Gate-Drain Charge		--	12	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	6.0	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	24	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 6 A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 6 A, dI_F / dt = 100 A/μs (Note 4)	--	630	--	ns
Q_{rr}	Reverse Recovery Charge		--	6.9	--	μC

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 34mH, I_{AS} = 6A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 6A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

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Typical Characteristics

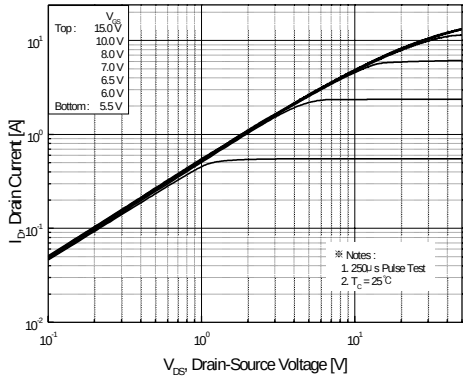

Figure 1. On-Region Characteristics

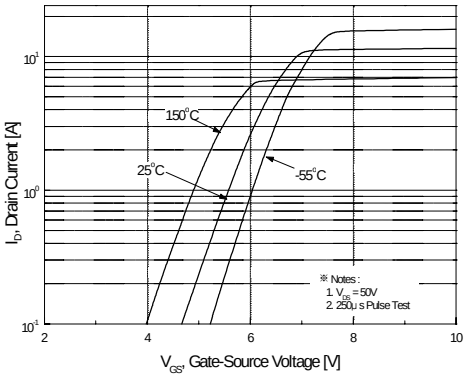

Figure 2. Transfer Characteristics

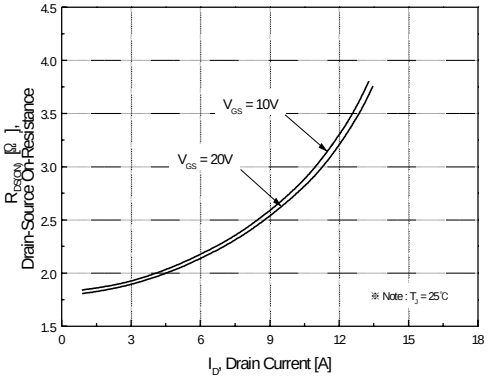

Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

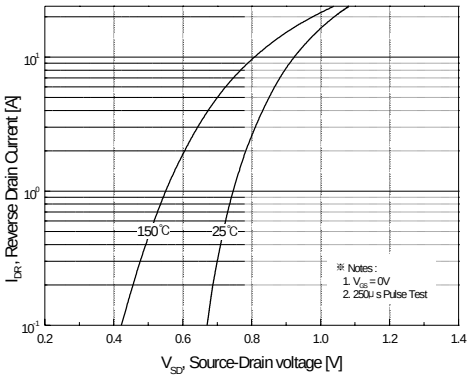

Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

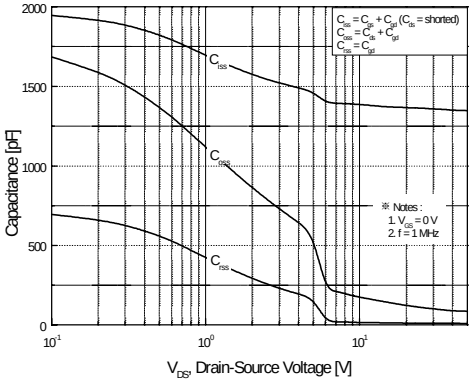

Figure 5. Capacitance Characteristics

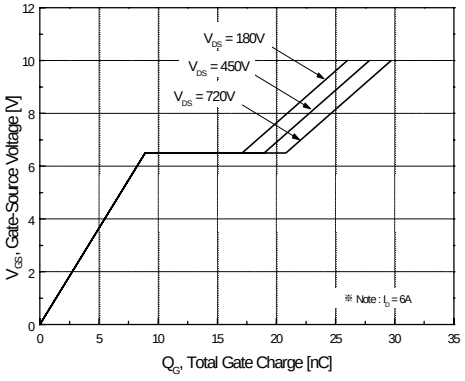

Figure 6. Gate Charge Characteristics

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Typical Characteristics (Continued)

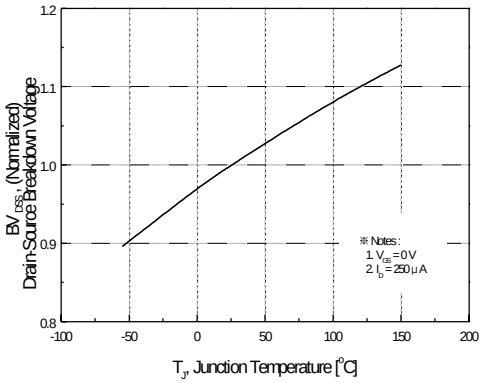

Figure 7. Breakdown Voltage Variation vs Temperature

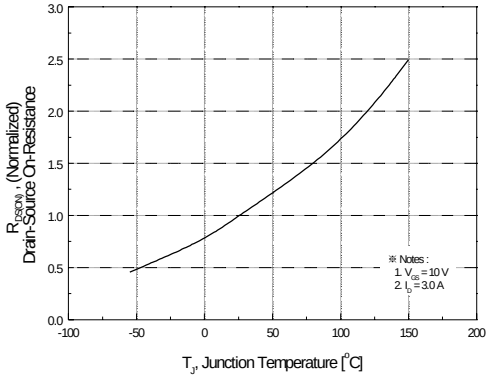

Figure 8. On-Resistance Variation vs Temperature

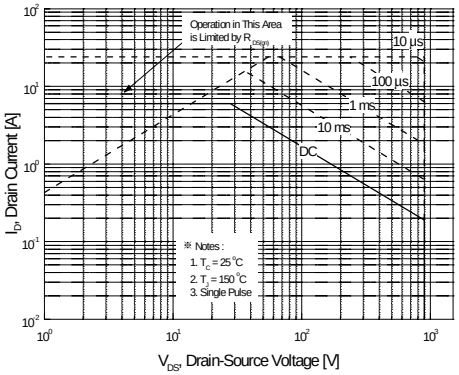

Figure 9-1. Maximum Safe Operating Area for FQP6N90C

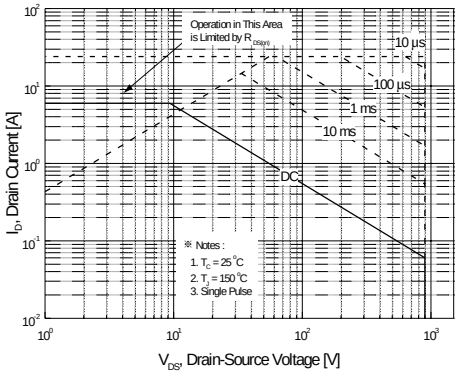

Figure 9-2. Maximum Safe Operating Area for FQPF6N90C

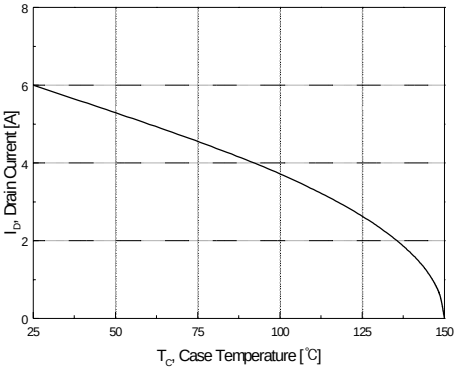

Figure 10. Maximum Drain Current vs Case Temperature

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Typical Characteristics (Continued)

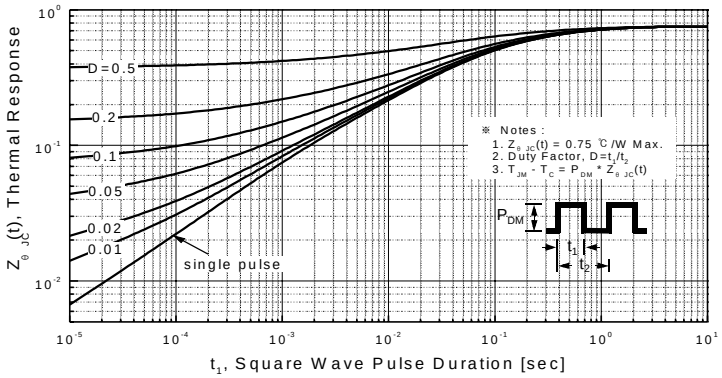

Figure 11-1. Transient Thermal Response Curve for FQP6N90C

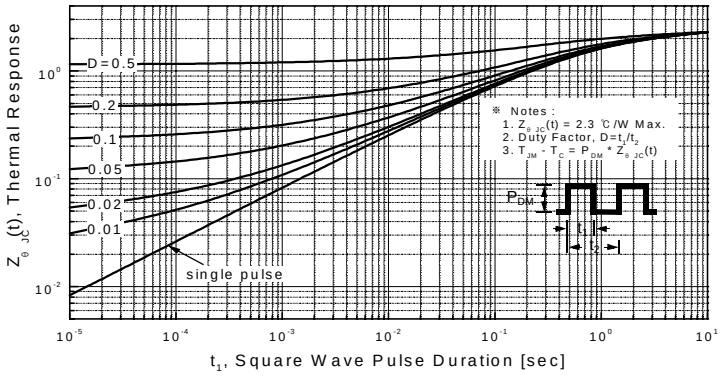

Figure 11-2. Transient Thermal Response Curve for FQPF6N90C

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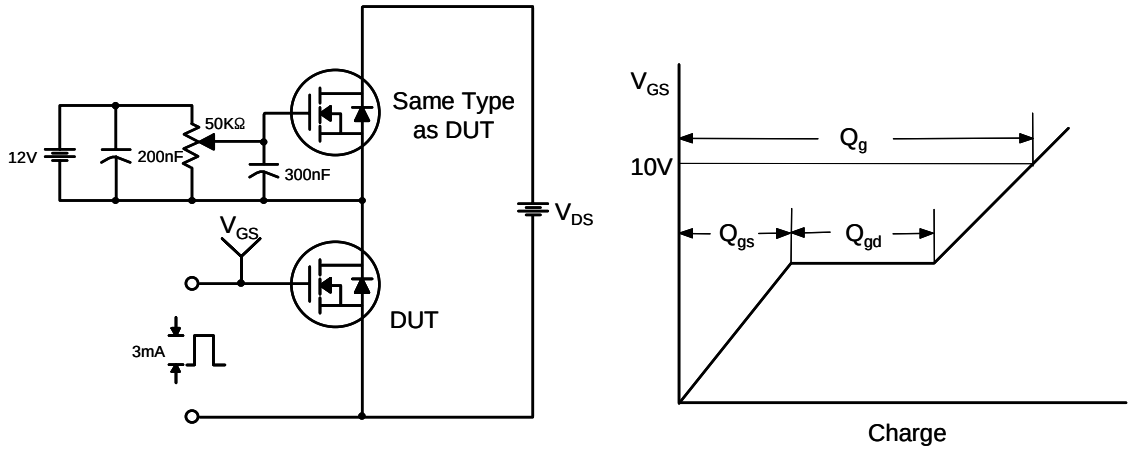
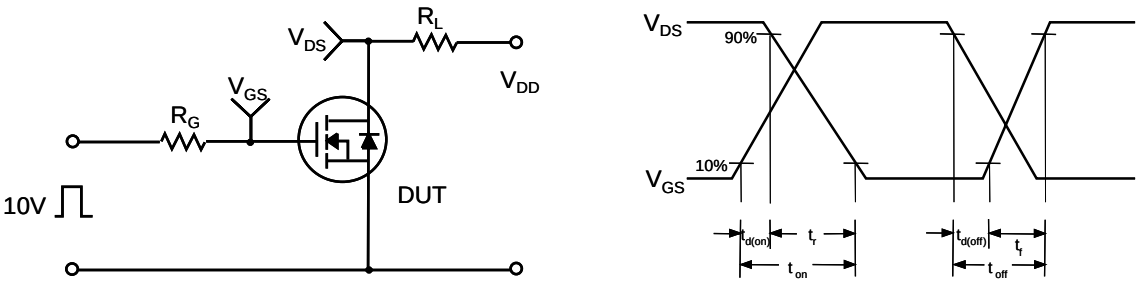
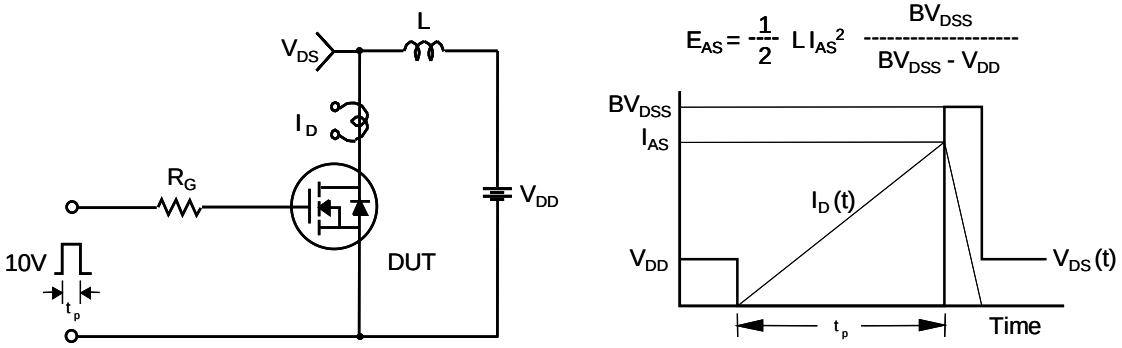
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



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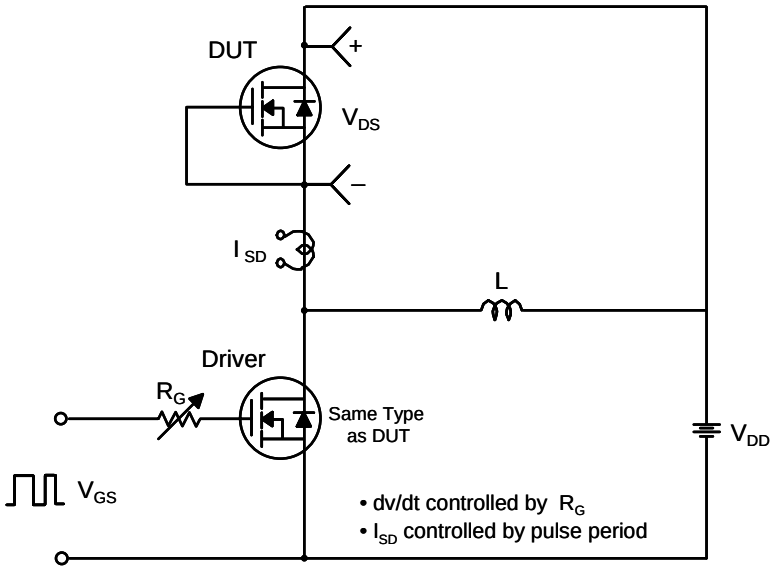
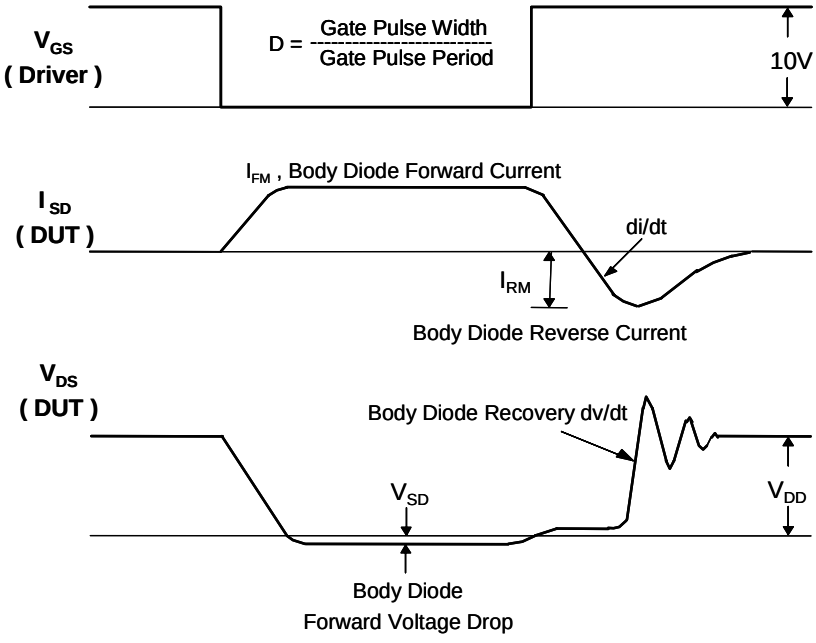
Peak Diode Recovery dv/dt Test Circuit & Waveforms





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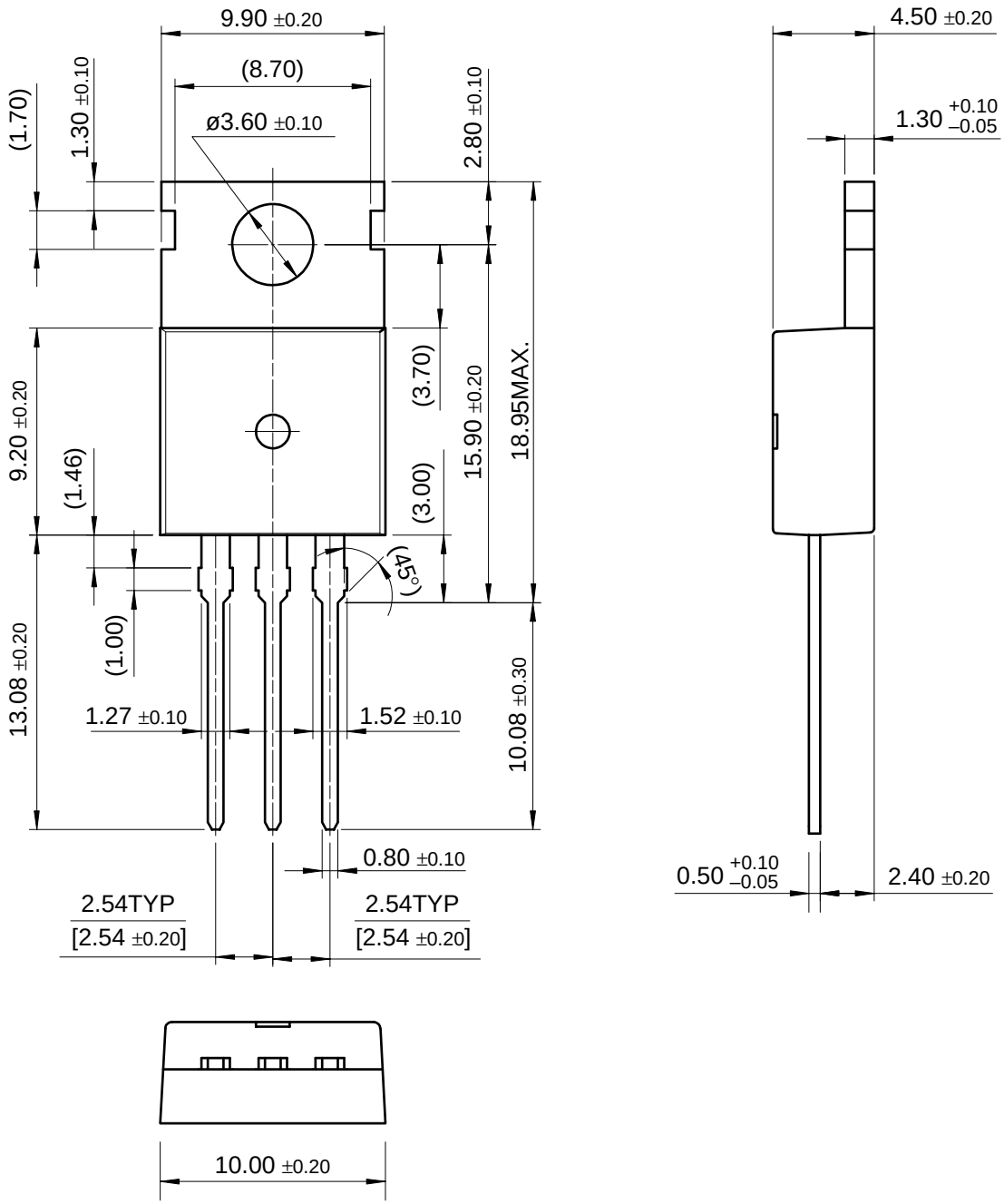
Package Dimensions

TO-220



Dimensions in Millimeters

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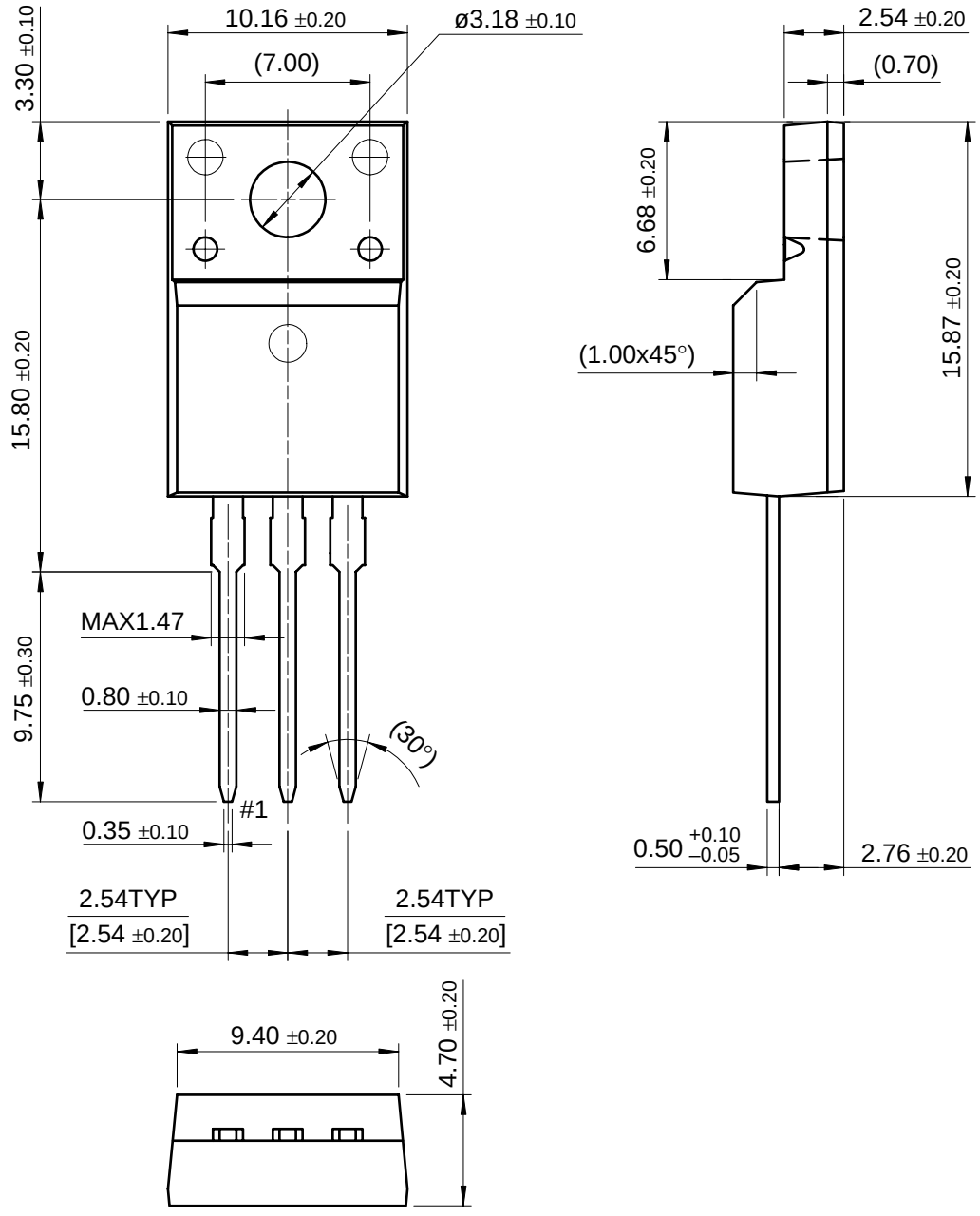
Package Dimensions (Continued)

TO-220F



Dimensions in Millimeters

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CoolFET™	FASTr™	MicroFET™	PowerTrench®	SuperSOT™-6
CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
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